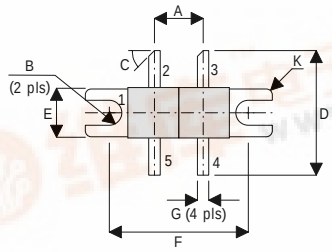
TetraFET

D2004UK

METAL GATE RF SILICON FET

MECHANICAL DATA



DK

PIN 1	SOURCE (COMMON)	PIN 2	DRAIN 1
PIN 3	DRAIN 2	PIN 4	GATE 2
PIN 5	GATE 1		

DIM	mm	Tol.	Inches	Tol.
A	6.45	0.13	0.254	0.005
B	1.65R	0.13	0.065R	0.005
C	45°	5°	45°	5°
D	16.51	0.76	0.650	0.03
E	6.47	0.13	0.255	0.005
F	18.41	0.13	0.725	0.005
G	1.52	0.13	0.060	0.005
H	4.82	0.25	0.190	0.010
I	24.76	0.13	0.975	0.005
J	1.52	0.13	0.060	0.005
K	0.81R	0.13	0.032R	0.005
M	0.13	0.02	0.005	0.001
N	2.16	0.13	0.085	0.005

GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 10W – 28V – 1GHz PUSH–PULL

FEATURES

- **SIMPLIFIED AMPLIFIER DESIGN**
- **SUITABLE FOR BROAD BAND APPLICATIONS**
- **VERY LOW C_{rss}**
- **SIMPLE BIAS CIRCUITS**
- **LOW NOISE**
- **HIGH GAIN – 10 dB MINIMUM**

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS from DC to 2 GHz

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

P_D	Power Dissipation	58W
BV_{DSS}	Drain – Source Breakdown Voltage *	65V
BV_{GSS}	Gate – Source Breakdown Voltage *	±20V
$I_{D(sat)}$	Drain Current *	2A
T_{stg}	Storage Temperature	–65 to 150°C
T_j	Maximum Operating Junction Temperature	200°C

* Per Side

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ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter		Test Conditions			Min.	Typ.	Max.	Unit
PER SIDE								
BV_{DSS}	Drain–Source Breakdown Voltage	V_{GS} = 0	I_D = 10mA		65			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 28V	V_{GS} = 0				0.4	mA
I_{GSS}	Gate Leakage Current	V_{GS} = 20V	V_{DS} = 0				1	µA
$V_{GS(th)}$	Gate Threshold Voltage *	I_D = 10mA	V_{DS} = V_{GS}		1		7	V
g_{fs}	Forward Transconductance *	V_{DS} = 10V	I_D = 0.4A		0.36			S
TOTAL DEVICE								
G_{PS}	Common Source Power Gain	P_O = 10W			10			dB
η	Drain Efficiency	V_{DS} = 28V	I_{DQ} = 0.4A		40			%
VSWR	Load Mismatch Tolerance	f = 1GHz			20:1			—
PER SIDE								
C_{iss}	Input Capacitance	V_{DS} = 0V	V_{GS} = –5V	f = 1MHz			24	pF
C_{oss}	Output Capacitance	V_{DS} = 28V	V_{GS} = 0	f = 1MHz			12	pF
C_{rss}	Reverse Transfer Capacitance	V_{DS} = 28V	V_{GS} = 0	f = 1MHz			1	pF

* Pulse Test: Pulse Duration = 300 µs , Duty Cycle ≤ 2%

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

$R_{THj–case}$	Thermal Resistance Junction – Case	Max. 3.0°C / W

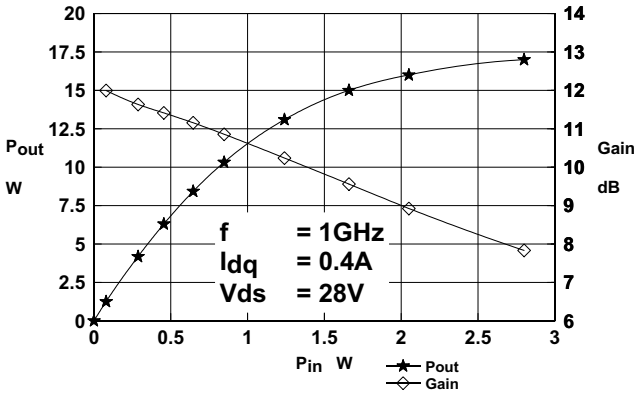

Figure 1
Output Power and Gain vs. Input Power

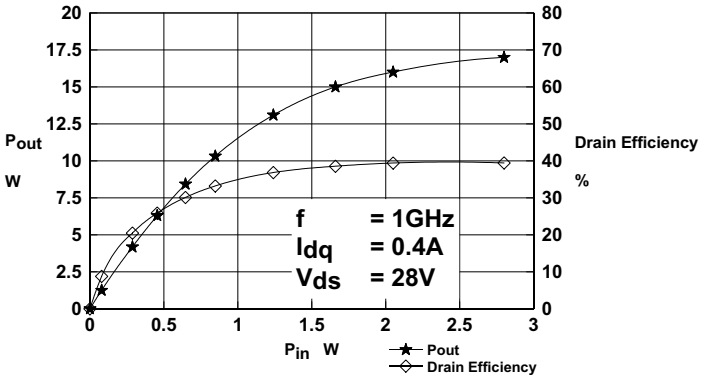

Figure 2
Output Power and Efficiency vs. Input Power.

OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency MHz	Z_S Ω	Z_L Ω
1000MHZ	2.4 - j2.5	5 + j1

N.B.

Impedances measured terminal to terminal.

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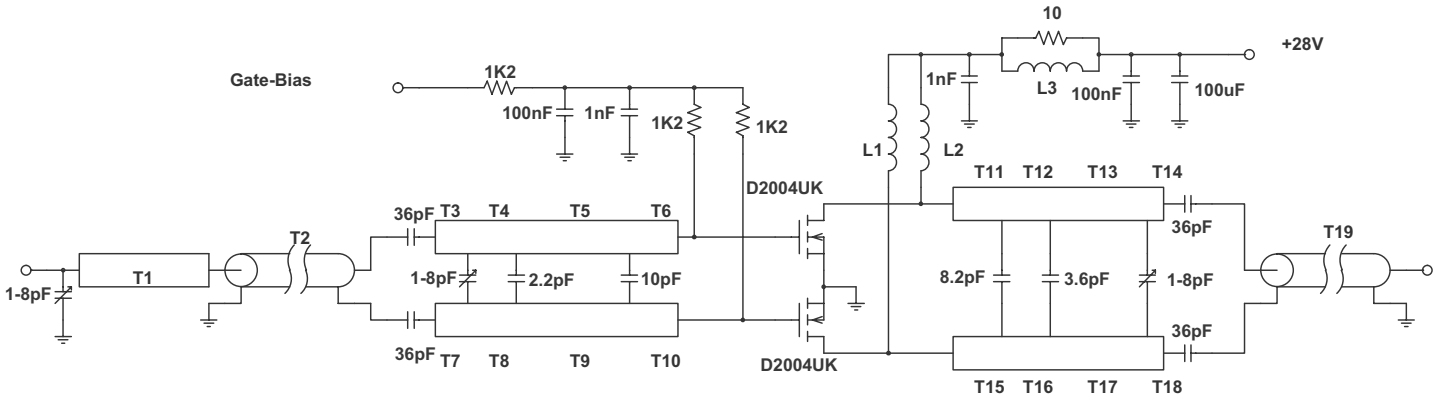

1000MHz TEST FIXTURE

Substrate 0.8mm thick PTFE/glass
All microstrip lines W = 2.7mm

T1	23 mm
T2, T19	50mm 50 OHM UT 34 semi-rigid coax
T3, T7	6mm
T4, T8	8mm
T5, T9	15mm
T6, T10	9mm
T11,T15	8mm
T12,T16	7mm
T13,T17	11mm
T14,T18	5mm

L1,L2	6 turns of 24swg enamelled copper wire, 3mm i.d.
L3	1.5 turns of 24swg enamelled copper wire on Siemens B62152-a7x 2 hole core